

General Description

The 078N03 uses advanced process technology and design to provide excellent $R_{DS(ON)}$. It can be used in a wide variety of applications.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

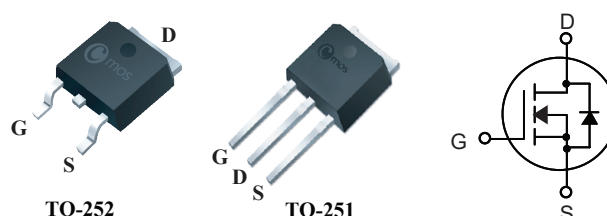
Product Summary

BVDSS	RDSON	ID
30V	7.8mΩ	65A

Applications

- DC/DC Converters in Computing
- Isolated DC/DC Converters in Telecom and Industrial

TO-252/251 Pin Configuration



Type	Package	Marking
CMD078N03	TO-252	CMD078N03
CMU078N03	TO-251	CMU078N03

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	65	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	45	A
I_{DM}	Pulsed Drain Current	260	A
EAS	Single Pulse Avalanche Energy ¹	56	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (6 cm ² cooling area)	---	50	°C/W
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	2.5	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	6.8	7.8	$m\Omega$
		$V_{GS}=4.5V$, $I_D=15A$	---	8.9	11	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=30V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	---	15	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge	$V_{DS}=15V$, $V_{GS}=0$ to $4.5V$ $I_D=30A$	---	8.7	---	nC
Q_{gs}	Gate-Source Charge		---	4.6	---	
Q_{gd}	Gate-Drain Charge		---	2.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=1.6\Omega$ $I_D=30A$	---	5	---	ns
T_r	Rise Time		---	4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	17	---	
T_f	Fall Time		---	3	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	650	---	pF
C_{oss}	Output Capacitance		---	200	---	
C_{rss}	Reverse Transfer Capacitance		---	30	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	65	A
I_{SM}	Pulsed Source Current		---	---	260	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$, $T_J=25^{\circ}\text{C}$	---	0.89	1.2	V

Note :

1.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=15A$.

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Typical Characteristics

